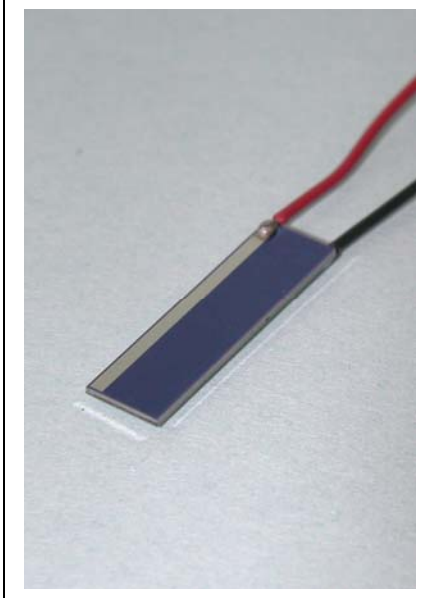
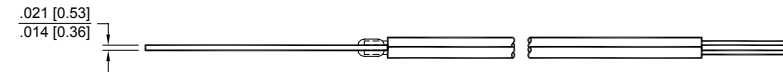
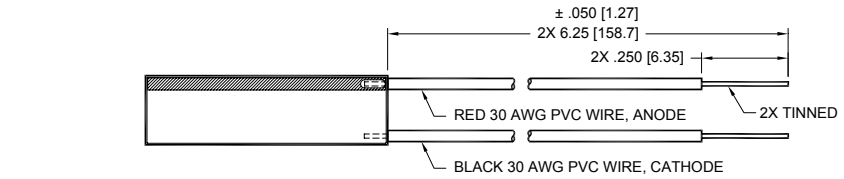
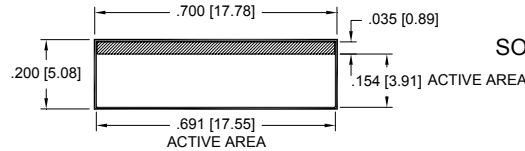




PACKAGE DIMENSIONS INCH [mm]



CHIP DIMENSIONS INCH [mm]



SOLDERABLE PHOTODIODE

FEATURES

- Red enhanced
- Photoconductive
- High quantum efficiency

DESCRIPTION

The **PDB-C612-2** is a silicon red enhanced solderable photodiode designed for low capacitance and high speed for photoconductive applications.

APPLICATIONS

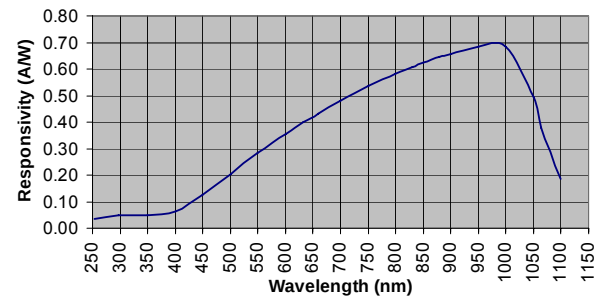
- Optical encoder
- Position sensor
- Industrial controls
- Instrumentation

ABSOLUTE MAXIMUM RATING (TA = 23°C UNLESS OTHERWISE NOTED)

| SYMBOL           | PARAMETER              | MIN | MAX  | UNITS |
|------------------|------------------------|-----|------|-------|
| V <sub>BR</sub>  | Reverse Voltage        |     | 75   | V     |
| T <sub>STG</sub> | Storage Temperature    | -40 | +125 | °C    |
| T <sub>O</sub>   | Operating Temperature  | -40 | +100 | °C    |
| T <sub>S</sub>   | Soldering Temperature* |     | +224 | °C    |

\* 1/16 inch from case for 3 seconds max.

SPECTRAL RESPONSE



ELECTRO-OPTICAL CHARACTERISTICS RATING (TA = 23°C UNLESS OTHERWISE NOTED)

| SYMBOL             | CHARACTERISTIC             | TEST CONDITIONS                 | MIN | TYP                 | MAX  | UNITS |
|--------------------|----------------------------|---------------------------------|-----|---------------------|------|-------|
| I <sub>SC</sub>    | Short Circuit Current      | H = 100 fc, 2850 K              | 810 | 900                 |      | μA    |
| I <sub>D</sub>     | Dark Current               | V <sub>R</sub> = 5 V            |     | 75                  | 150  | nA    |
| R <sub>SH</sub>    | Shunt Resistance           | V <sub>R</sub> = 10 mV          | 5   | 10                  |      | MΩ    |
| C <sub>J</sub>     | Junction Capacitance       | V <sub>R</sub> = 5 V, f = 1 MHz |     | 240                 |      | pF    |
| λ <sub>range</sub> | Spectral Application Range | Spot Scan                       | 350 |                     | 1100 | nm    |
| V <sub>BR</sub>    | Breakdown Voltage          | I = 10 μA                       | 25  | 50                  |      | V     |
| NEP                | Noise Equivalent Power     | V <sub>R</sub> = 0V @ λ = Peak  |     | 7x10 <sup>-13</sup> |      | W/√Hz |
| t <sub>r</sub>     | Response Time              | RL = 1KΩ, V <sub>R</sub> = 5V   |     | 45                  |      | nS    |

\*\*Response time of 10% to 90% is specified at 660nm wavelength light.

Information in this technical datasheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice.